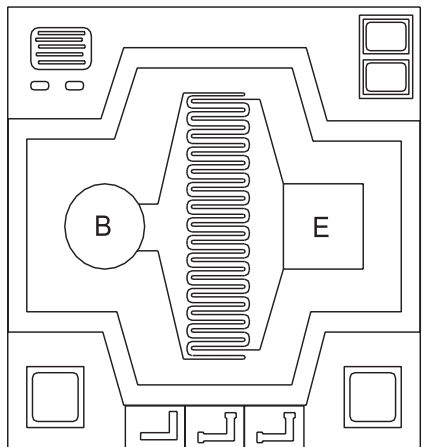


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	22 x 22 MILS
Die Thickness	8.0 MILS
Base Bonding Pad Area	3.5 MILS DIAMETER
Emitter Bonding Pad Area	3.5 x 3.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

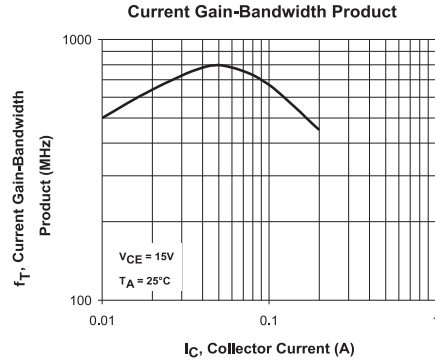
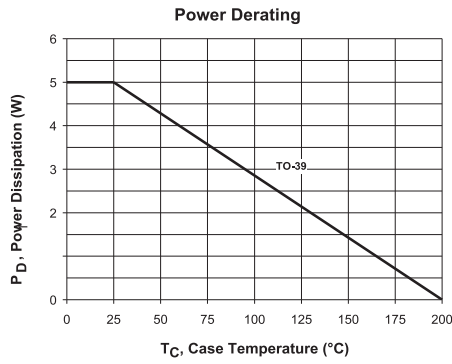
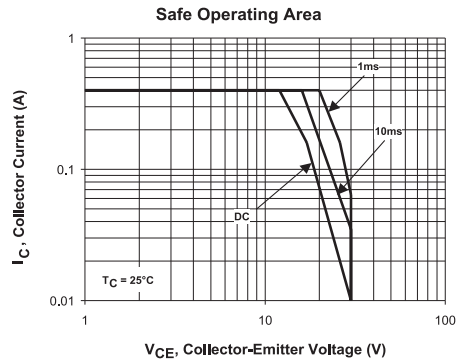
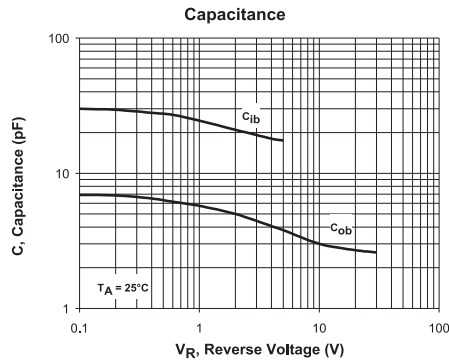
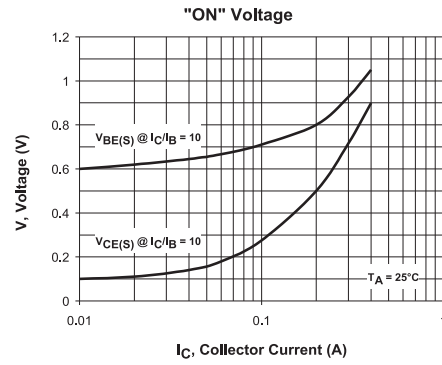
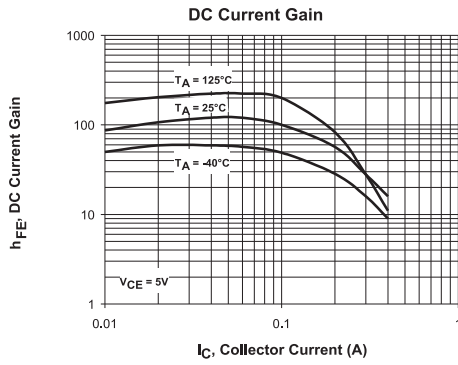
23,340

PRINCIPAL DEVICE TYPES

2N3866

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R1 (1-August 2002)



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